

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC2710

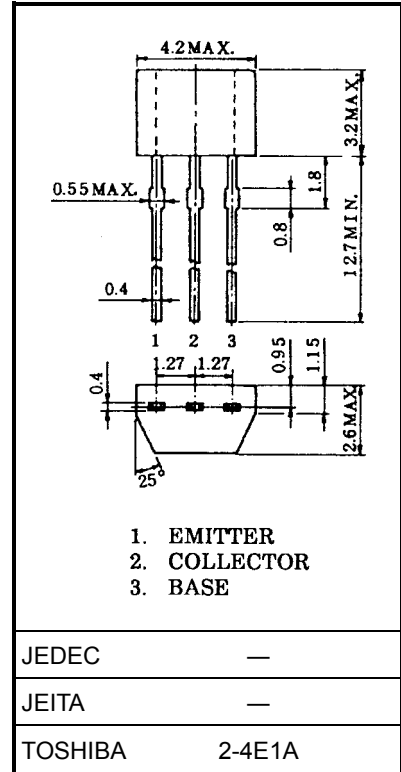
For Audio Amplifier Applications

- High DC current gain: $h_{FE(1)} = 100\sim 320$
- Complementary to 2SA1150

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	35	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	mA
Base current	I_B	160	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Unit: mm



Electrical Characteristics (Ta = 25°C)

Weight: 0.13 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 35\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	30	—	—	V
DC current gain	$h_{FE(1)}$ (Note)	$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = 1\text{ V}, I_C = 700\text{ mA}$	35	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{ mA}, I_B = 20\text{ mA}$	—	—	0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}$	0.5	—	0.8	V
Transition frequency	f_T	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	—	120	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	13	—	pF

Note: $h_{FE(1)}$ classification O: 100~200, Y: 160~320

